ABSTRACT

METHODS AND APPARATUS FOR A WIDE CONDUCTANCE KIT

An apparatus for controlling gas flow conductance in a plasma processing chamber being configured with an upper electrode disposed opposite a lower electrode adapted to support a substrate is provided. The apparatus includes a ground ring configured to include a first set of radial slots formed therein. The apparatus also includes a confinement ring arrangement which includes at least a first set of collapsible confinement rings and a second set of collapsible confinement rings which is configured to movably couple to the first set of collapsible confinement rings. The apparatus further includes a mechanism configured at least to collapse and to expand the first set of collapsible confinement rings and the second set of collapsible confinement rings to control gas flow conductance through the first set of radial slots between (a) an unobstructed gas flow, ON state, and (b) an obstructed gas flow, OFF state.

FIG. 3A